

# **FQP27P06 Information**



For Reference Only

Part Number FQP27P06

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 60V 27A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **FQP27P06 Specifications**

Manufacturer Part Number         FQP27P06           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         27A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         43nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1400pF @ 25V           Vgs (Max)         25V           FET Feature         -           Power Dissipation (Max)         120W (Tc)           Rds On (Max) @ Id, Vgs         70 mOhm @ 13.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         27A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         43nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1400pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         120W (Tc)           Rds On (Max) @ Id, Vgs         70 mOhm @ 13.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3	Manufacturer Part Number	FQP27P06
Package         TO-220-3           Series         QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         27A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         43nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1400pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         120W (Tc)           Rds On (Max) @ Id, Vgs         70 mOhm @ 13.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3	Manufacturer	Fairchild/ON Semiconductor
Package         TO-220-3           Series         QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         27A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         43nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1400pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         120W (Tc)           Rds On (Max) @ Id, Vgs         70 mOhm @ 13.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3	Category	Discrete Semiconductor Products
Series         QFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         27A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         43nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1400pF @ 25V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         120W (Tc)           Rds On (Max) @ Id, Vgs         70 mOhm @ 13.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Series	QFET?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C27A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs43nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1400pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  43nC @ 10V  1400pF @ 25V  +25V  FET Feature  -  Nond 120W (Tc)  70 mOhm @ 13.5A, 10V  -55°C ~ 175°C (TJ)  Through Hole  TO-220-3  TO-220-3	Current - Continuous Drain (Id) @ 25°C	27A (Tc)
Gate Charge (Qg) (Max) @ Vgs 43nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1400pF @ 25V  Vgs (Max) ±25V  FET Feature - Power Dissipation (Max) 120W (Tc)  Rds On (Max) @ Id, Vgs 70 mOhm @ 13.5A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  1400pF @ 25V  Vgs (Max)  ET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  70 mOhm @ 13.5A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±25VFET Feature-Power Dissipation (Max)120W (Tc)Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	43nC @ 10V
FET Feature - 120W (Tc)  Rds On (Max) @ Id, Vgs 70 mOhm @ 13.5A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1400pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  70 mOhm @ 13.5A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220-3  Package / Case  TO-220-3	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs70 mOhm @ 13.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3	Power Dissipation (Max)	120W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	70 mOhm @ 13.5A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

## **FQP27P06 Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **FQP27P06 Payment Methods**



















### **FQP27P06 Shipping Methods**













If you have any question about FQP27P06, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com